

Search History (8pp.) ~~10/2/05~~ 10/2/05.

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	channel near6 (zinc adj tin adj oxide ("zn.sub."\$3 near1 "sn" near1 "O.sub."\$3 ("zn.sub."\$3"sn"\$1"o.sub."\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 17:44
L2	2	channel near6 (zinc adj stannate zinc adj tin adj oxide ("zn.sub."\$3 near1 "sn" near1 "O.sub."\$3 ("zn.sub."\$3"sn"\$1"o.sub."\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 17:45
L3	2	channel near6 (stannate zinc adj stannate zinc adj tin adj oxide ("zn.sub."\$3 near1 "sn" near1 "O.sub."\$3 ("zn.sub."\$3"sn"\$1"o.sub."\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 17:45
L5	4	"763353".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 17:58
L6	26	channel near8 (oxide near8 zinc near8 tin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 18:07
L7	26	channel near8 (oxide near8 zinc near8 tin stannate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 18:08
L8	89	(semiconductor adj (layer film) channel) near8 (oxide near8 zinc near8 tin stannate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 18:08
L9	15	(semiconductor adj (layer film) channel) near8 (oxide near8 zinc near8 tin stannate) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 18:08
L10	1	(US-20050017244-\$).did	US-PGPUB	OR	OFF	2005/10/01 19:12
L11	2	thin adj film adj transistor and zto	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 19:16

L12	0	"574464".pn. and electrode near6 ITO	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 20:14
L13	377	thin adj film adj transistor and (dielectric gate adj insulati\$2) near6 (sapphire alumin\$1um adj oxide titanium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:15
L14	42	thin adj film adj transistor.ti,ab, clm. and (gate adj (oxide insulati\$2)) near4 (sapphire alumin\$1um adj oxide titanium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:19
L15	4	thin adj film adj transistor.ti,ab, clm. and (gate adj (oxide insulati\$2)) near4 (sapphire alumin\$1um adj oxide titanium adj oxide) and first adj insulati\$2 and second adj insulati\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:21
L16	5	thin adj film adj transistor.ti,ab, clm. and gate adj (oxide insulati\$2) near6 titanium adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:22
L17	41	thin adj film adj transistor.ti,ab, clm. and gate adj (oxide insulati\$2) near6 (alumin\$1um adj oxide titanium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:22
L18	0	thin adj film adj transistor.ti,ab, clm. and (gate adj (oxide insulati\$2) near6 (alumin\$1um adj oxide) near6 (titanium adj oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:24
L19	0	thin adj film adj transistor.ti,ab, clm. and (gate adj (oxide insulati\$2)) near6 (lamine) near6 titanium near6 aluminum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:24

L20	0	(field adj effect adj transistor MOSFET MOS thin adj film adj transistor).ti,ab,clm. and (gate adj (oxide insulati\$2)) near6 (lamine) near6 titanium near6 aluminum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:25
L21	34	(field adj effect adj transistor MOSFET MOS thin adj film adj transistor).ti,ab,clm. and (gate adj (oxide insulati\$2)) near6 titanium near6 aluminum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:30
L22	13	(field adj effect adj transistor MOSFET MOS thin adj film adj transistor).ti,ab,clm. and (gate adj (oxide insulati\$2)) near6 titanium adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:19
L23	0	(field adj effect adj transistor MOSFET MOS thin adj film adj transistor).ti,ab,clm. and (gate adj (oxide insulati\$2)) near6 titanium adj oxide and (gate adj (oxide insulati\$2)) near6 alumin\$1um adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:32
L24	36	(field adj effect adj transistor MOSFET MOS thin adj film adj transistor).ti,ab,clm. and (gate adj (oxide insulati\$2)) near6 alumin\$1um adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 20:32
L25	2	jp-60198861\$-\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:43
L26	473	transparent adj gate adj electrode and transparent drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:45
L27	157	transparent adj gate adj electrode and transparent drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel and zto	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:46

L28	157	transparent adj gate adj electrode and transparent drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel and zto and zinc and tin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:46
L29	157	transparent adj gate adj electrode and transparent drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel and zto and zinc and tin and "zn.sub.2sno.sub.4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:47
L30	0	transparent adj gate adj electrode and transparent near2 drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel and zto and zinc and tin and "zn.sub.2sno.sub.4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:48
L31	0	transparent near2 gate adj electrode and transparent near2 drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel and zto and zinc and tin and "zn.sub.2sno.sub.4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:48
L32	0	transparent near2 gate adj electrode and transparent near2 drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:48
L33	0	transparent near2 gate and transparent near2 drain adj electrode and active adj matrix adj display.ti,ab,clm. and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:48
L34	291	transparent near2 electrode and active adj matrix adj display.ti,ab,clm. and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:48
L35	264	transparent near2 electrode and active adj matrix adj display.ti,ab,clm. and pixel and (thin adj film adj transistor tft)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:49

L36	161	transparent near2 electrode and active adj matrix adj display.ti,ab,clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:49
L37	0	transparent near2 electrode and active adj matrix adj display.ti,ab,clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm. and zto	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:49
L38	0	transparent near2 electrode and active adj matrix adj display.ti,ab,clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm. and (zinc adj tin adj oxide zto)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:50
L39	106	transparent near2 electrode and active adj matrix adj display.ti,ab,clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm. and (zinc adj tin adj oxide zto zinc adj oxide tin adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 21:50
L40	52	transparent near2 electrode and active adj matrix adj display.ti,ab,clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm. and (zinc adj tin adj oxide zto zinc adj oxide tin adj oxide) and transparent.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 22:22
L41	0	transparent near2 electrode and active adj matrix adj display.ti,ab,clm. and pixel and (thin adj film adj transistor tft).ti,ab,clm. and (zinc adj tin adj oxide zto zinc adj oxide tin adj oxide) and transparent.ti,ab,clm. and enhancement adj mode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 22:22

L42	37	(US-20020153587-\$ or US-20020171085-\$ or US-20030013261-\$ or US-20030104659-\$ or US-20030139026-\$ or US-20030180996-\$ or US-20030186489-\$ or US-20030207502-\$ or US-20030218221-\$ or US-20030218222-\$ or US-20030219530-\$ or US-20030224550-\$ or US-20050017244-\$ or US-20050199881-\$ or US-20050199880-\$ or US-20050017302-\$ or US-20040061136-\$ or US-20050040756-\$ or US-20020051099-\$).did. or (US-4559238-\$ or US-4589026-\$ or US-4887255-\$ or US-5107314-\$ or US-5470768-\$ or US-5744864-\$ or US-5879973-\$ or US-6255130-\$ or US-6255655-\$ or US-6362499-\$ or US-6391462-\$ or US-6561174-\$ or US-6569720-\$).did. or (EP-40076-\$).did. or (JP-60198861-\$).did. or (US-20050017244-\$ or US-20030218221-\$ or US-20030218222-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/01 22:23
L43	17	enhancement adj mode.ti,ab,clm. and thin adj film adj transistor.ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 22:25
L44	0	enhancement adj mode.ti,ab,clm. and thin adj film adj transistor.ti, ab,clm. and address adj TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 22:25
L45	0	enhancement adj mode.ti,ab,clm. and thin adj film adj transistor.ti, ab,clm. and (switching address) adj TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 22:26
L46	4611	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/02 00:13



L47	2	46 and ("zn.sub."\$3"sn"\$1"o.sub.4" zinc adj stannate zto "zn.sub."\$3 near1 "sn" near1 "o.sub."\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 00:17
L48	2	46 and ("zn.sub."\$3"sn"\$1"o.sub.4" zinc adj stannate zto "zn.sub."\$3 near1 "sn" near1 "o.sub."\$3 zto)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 23:29
L49	7877	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/213) or (257/288) or (257/390) or (257/403)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/02 00:16
L50	2	49 and ("zn.sub."\$3"sn"\$1"o.sub.4" zinc adj stannate zto "zn.sub."\$3 near1 "sn" near1 "o.sub."\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 00:17
S1	3	((("5,470,768") or ("5,879,973") or ("6,569,720"))).PN.	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/10/01 16:45
S2	20	((("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:48
S3	10	((("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:53
S4	1	("20030013261").PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:52
S5	11	S3 S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:53

S6	9	((("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462"))).PN. or ((2002/0153587) or (2002/0171085)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:56
S7	11	((("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462") or ("20020153587") or ("20020171085"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:57
S8	0	ep-0040076\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:58
S9	0	ep-00040076\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:59
S10	82	sasano.in.	EPO	OR	OFF	2005/10/01 17:02
S11	0	sasano.in. and drain and compound	EPO	OR	OFF	2005/10/01 17:01
S12	0	sasano.in. and drain	EPO	OR	OFF	2005/10/01 17:02
S13	4	sasano.in. and semiconductor	EPO	OR	OFF	2005/10/01 17:02
S14	1	(EP-40076-\$).did.	EPO	OR	OFF	2005/10/01 17:08
S15	4	((("5,744,864") or ("20020101557"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 17:08
S16	2	((("5,744,864") or ("20020101557"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 17:08